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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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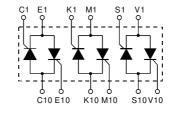


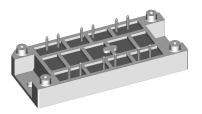
s I_{RM}

I_{RMS} = 3x 83 A V_{RRM} = 800-1600 V

Preliminary data

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Туре
v	V	
800	800	VWO 85-08io1
1200	1200	VWO 85-12io1
1400	1400	VWO 85-14io1
1600	1600	VWO 85-16io1





Symbol	Test Conditions	ons Max. Ratings per phase			
I _{RMS} I _{RMS} I _{TAVM}	$T_{c} = 85^{\circ}C, 50 - 400$ $T_{c} = 85^{\circ}C, 50 - 400$ $T_{c} = 85^{\circ}C; (180^{\circ} \text{ si})$) Hz (per phase) for 10 sec.	59 83 27	A A A	
I _{TSM}	$\begin{array}{l} T_{_{VJ}}=45^{\circ}C;\\ V_{_{\mathrm{R}}}=0 \end{array}$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 560	A A	
	$T_{VJ} = 125^{\circ}C$ $V_{B} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	470 510	A A	
l²t	$T_{\rm VJ} = 45^{\circ}\rm C$ $V_{\rm R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 1320	A²s A²s	
	$T_{VJ} = 125^{\circ}C$ $V_{R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1100 1090	A²s A²s	
(di/dt) _{cr}	T _{vJ} =125°C f =50 Hz, t _p =200 µ V _D = 2/3 V _{DRM}	repetitive, $I_{T} = 45 \text{ A}$ us	150	A/µs	
	I _G ⁻ = 0.45 A	non repetitive, $I_T = I_{TAVM}$	500	A/μs	
(dv/dt) _{cr}	$T_{VJ} = 125^{\circ}C;$ $R_{GK} = \infty;$ method 1	$V_{DR} = 2/3 V_{DRM}$ (linear voltage rise)	1000	V/µs	
		$t_{p} = 30 \ \mu s$	10	W	
	$I_T = I_{TAVM}$	E Contraction of the second se		W	
P _{GAVM}		r	0.5	W	
V _{rgm}			10	V	
T _{VJ} T _{VIM}	for 10 sec.		-40+125 150	°C ℃	
T _{stg}			-40+125	°C	
V _{ISOL}	50/60 Hz, RMS	t = 1 min	3000	V~	
	$I_{ISOL} \le 1 \text{ mA}$	t = 1 s	3600	V~	
M _d	Mounting torque (M	15)	2-2.5 18-22	Nm. lb.in.	
Weight	typ.		80	g	

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Package with DCB base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- UL applied

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- · Light and temperature control

Advantages

- · Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling
- High power density

Data according to IEC 60747 refer to a single thyristor unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.



Symbol	Test Conditions 0	Characteristic Values		
I _D , I _R	$T_{vJ} = 125^{\circ}C; V_{R} = V_{RRM}; V_{D} = V_{DRM}$	≤	5	mA
V _T	$I_{T} = 85 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$	≤	1.67	V
V _{T0}	For power-loss calculations only		0.85	V
r			11	mΩ
V _{gt}	$V_{\rm p} = 6 \text{ V};$ $T_{\rm vl} = 25^{\circ}\text{C}$	\leq	1.5	V
GI	$T_{v,i}^{v} = -40^{\circ}C$	\leq	1.6	V
I _{GT}	$V_{\rm D} = 6 \text{ V};$ $T_{\rm VJ}^{\circ} = 25^{\circ}\text{C}$	\leq	100	mA
	$T_{vJ}^{v3} = -40^{\circ}C$	\leq	200	mA
V _{GD}	$T_{V_{L}} = 125^{\circ}C;$ $V_{D} = 2/3 V_{DBM}$	\leq	0.2	V
		\leq	5	mA
I.	$T_{yy} = 25^{\circ}C; t_{p} = 10 \ \mu s$	≤	450	mA
	l _g [°] = 0.45 A; di _g /dt = 0.45 A/μs			
I _H	$T_{_{VJ}}$ = 25°C; $V_{_{D}}$ = 6 V; $R_{_{GK}}$ = ∞	\leq	200	mA
t _{gd}	$T_{VJ} = 25^{\circ}C; V_{D} = 1/2 V_{DRM}$ $I_{G} = 0.45 A; di_{G}/dt = 0.45 A/\mu s$	≤	2	μS
t _q	$ \begin{array}{l} T_{_{VJ}} \!$	us typ.	150	μS
R _{thJC}	per thyristor		0.92	K/W
100	per module		0.154	K/W
R _{thJK}	per thyristor		1.22	K/W
	per module		0.204	K/W
ds	Creeping distance on surface		12.7	mm
d _s d _a	Creepage distance in air		9.4	mm
ລົ	Max. allowable acceleration		50	m/s ²

Dimensions in mm (1 mm = 0.0394")

